

a protective film [covering] over said third metal layer, said protective film [covering exposing] leaving exposed a central portion of said third metal layer;

said electrode layer being capable of passing an emitted light;

said electrode pad being capable of supplying a current to said electrode layer; and

wherein said second metal layer is made of gold (Au), said first metal layer comprises a material that has an ionization potential lower than gold (Au), and said third metal layer comprises aluminum (Al) that has an adhesiveness to said protection film which is stronger than gold (Au)[.], said second metal layer being distributed more deeply into said semiconductor than that of said first metal layer by heat treatment.

10. (Twice Amended) The light-emitting semiconductor device according to claim 1, further comprising:

[a semiconductor layer] semiconductor layers having Group III nitride compound semiconductor and satisfying the formula,  $Al_xGa_yIn_{1-x-y}N$ , wherein  $[0 < x < 1, 0 < y < 1, \text{ and } 0 < x + y < 1]$   $0 \leq x \leq 1, 0 \leq y \leq 1, \text{ and } 0 \leq x + y \leq 1$ .

11. (Twice Amended) The light-emitting semiconductor device according to claim 10, wherein said device is one of a light-emitting diode (LED)[,] and a light-emitting laser diode (LD) [and a transistor].

22. (Amended) The light-emitting semiconductor device according to claim 12, wherein said electrode pad comprises:

a first metal layer formed on said surface layer, a second metal layer formed on said first metal layer, and a third metal layer formed on said second metal layer; [and] said device further comprising: